

2SJ668(TE16L1,NQ)

2SJ668(TE16L1,NQ) Information

Cold Heisener.com	Part Number	2SJ668(TE16L1,NQ)	
	Manufacturer	Toshiba Semiconductor and Storage	
	Category	Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single	
	Description	MOSFET P-CH 60V 5A PW-MOLD	1 2 -3
	Package	TO-252-3, DPak (2 Leads + Tab), SC-63	- 65
		For the pricing/inventory/lead time, please contact	E 12/
For Reference Only		us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Reque

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Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



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2SJ668(TE16L1,NQ) Specifications

Manufacturer Part Number 2SI668(TE16L1,NQ) Manufacturer Toshiba Semiconductor and Storage Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series U-MOSIII FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgt(h (Max) @ Id 2V @ ImA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2000F @ 10V Vgs (Max) 20W (Tc) Rds On (Max) @ Id, Vgs 170 mOhm @ 2.5A, 10V Operating Temperature 150°C Mounting Type Surface Mount Supplier Device Package PW-MOLD Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesU-MOSIIIFET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 1mAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds20W (Tc)FET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs150°CMounting TypeSurface MountMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	2SJ668(TE16L1,NQ)
Transistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesU-MOSIIIFET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 1mAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds700pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)0W (Tc)Rds On (Max) @ Id, Vgs150°CMounting TypeSurface MountSurplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer	Toshiba Semiconductor and Storage
PackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesU-MOSIIIFET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ ImAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds700pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Category	Discrete Semiconductor Products
SeriesU-MOSIIIFET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 1mAGate Charge (Qg) (Max) @ Vgs15n C @ 10VInput Capacitance (Ciss) (Max) @ Vds200 F @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)00W (Tc)Rds On (Max) @ Id, Vgs150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTo-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelFET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C5A (Ta)Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 1mAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds700pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)0W (Tc)Rds On (Max) @ Id, Vgs100mm @ 2.5A, 10VOperating Temperature50°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTo-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 700pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 20W (Tc) Rds On (Max) @ Id, Vgs 170 mOhm @ 2.5A, 10V Operating Temperature 150°C Mounting Type Surface Mount Supplier Device Package PW-MOLD Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Series	U-MOSIII
Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 700pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 20W (Tc) Rds On (Max) @ Id, Vgs 170 mOhm @ 2.5A, 10V Operating Temperature 150°C Mounting Type Surface Mount Supplier Device Package PW-MOLD Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 700pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 0W (Tc) Rds On (Max) @ Id, Vgs 170 mOhm @ 2.5A, 10V Operating Temperature Surface Mount Mounting Type Surface Mount Supplier Device Package PW-MOLD Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4V, 10VVgs(th) (Max) @ Id2V @ 1mAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds700pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating TemperatureSurface MountMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	60V
Ygs(th) (Max) @ Id 2V @ 1mA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 700pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 02W (Tc) Rds On (Max) @ Id, Vgs 170 mOhm @ 2.5A, 10V Operating Temperature 150°C Mounting Type Surface Mount Supplier Device Package PW-MOLD Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	5A (Ta)
Gate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds700pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO -252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	4V, 10V
Input Capacitance (Ciss) (Max) @ Vds700pF @ 10VVgs (Max)±20VFET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	2V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	15nC @ 10V
FET Feature-Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	700pF @ 10V
Power Dissipation (Max)20W (Tc)Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs170 mOhm @ 2.5A, 10VOperating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature150°CMounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	20W (Tc)
Nounting TypeSurface MountSupplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	170 mOhm @ 2.5A, 10V
Supplier Device PackagePW-MOLDPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	150°C
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	PW-MOLD
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

2SJ668(TE16L1,NQ) Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

2SJ668(TE16L1,NQ) Payment Methods





If you have any question about 2SJ668(TE16L1,NQ), please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com